

isc Silicon PNP Power Transistor

2SA1061

DESCRIPTION

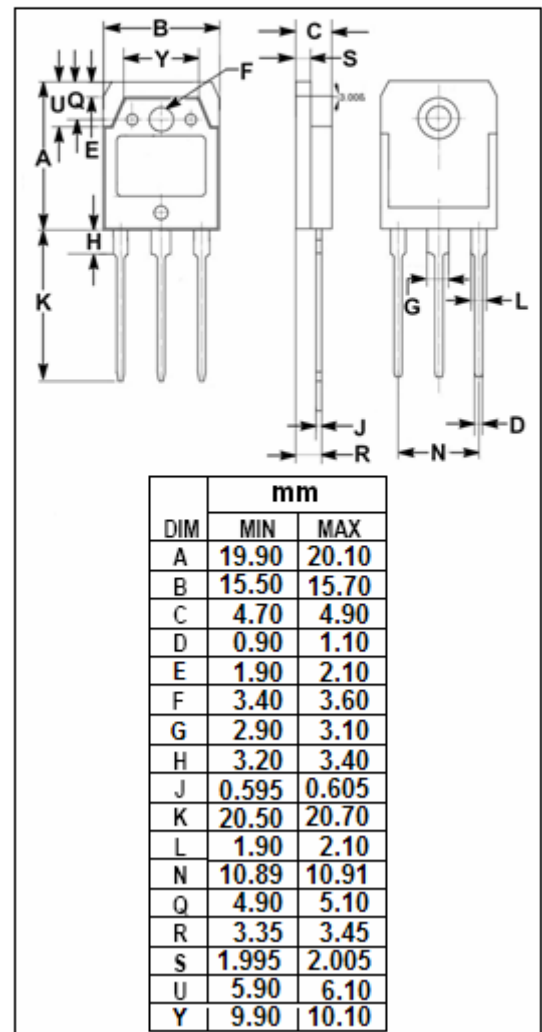
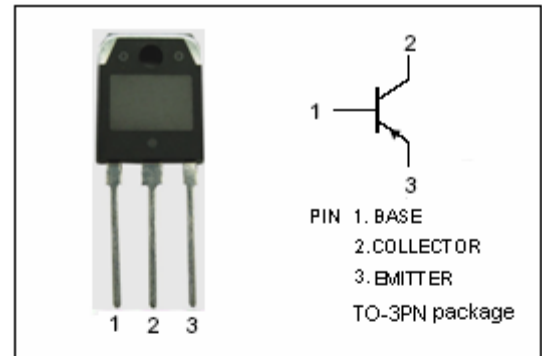
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -100V(\text{Min})$
- High Power Dissipation
- Complement to Type 2SC2485

APPLICATIONS

- Designed for high power audio frequency amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-6	A
I_{CM}	Collector Current-Peak	-10	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	70	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor**2SA1061****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -30\text{mA}$; $I_B = 0$	-100			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -4\text{A}$; $I_B = -0.4\text{A}$			-2.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -4\text{A}$; $V_{CE} = -5\text{V}$			-1.8	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -100\text{V}$; $I_E = 0$			-50	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -3\text{V}$; $I_C = 0$			-50	μA
h_{FE-1}	DC Current Gain	$I_C = -0.2\text{A}$; $V_{CE} = -5\text{V}$	20			
h_{FE-2}	DC Current Gain	$I_C = -1\text{A}$; $V_{CE} = -5\text{V}$	40		220	
h_{FE-3}	DC Current Gain	$I_C = -4\text{A}$; $V_{CE} = -5\text{V}$	20			
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}$; $V_{CE} = -5\text{V}$		20		MHz

◆ **h_{FE-2} Classifications**

R	Q	P
40-80	60-120	100-200